ERRATUM

Erratum to: A study on the competition between bias-induced charge trapping and light-induced instability in In-Ga-Zn-O thin-film transistors

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The name of the third author should be displayed as Yang Soo Kim (as shown above), not Soo Kim Yang.
The original article was corrected.

The online version of the original article can be found at <http://dx.doi.org/10.1007/s10832-016-0032-3>.

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